

EVVOSEMI[®]

THINK CHANGE DO



ESD



TVS



MOS



LDO



Diode



Sensor



DC-DC

Product Specification

▶ Domestic	Part Number	IRLZ34N
▶ Overseas	Part Number	IRLZ34N
▶ Equivalent	Part Number	IRLZ34N

EV is the abbreviation of name EVVO

60V N-Channel Enhancement Mode MOSFET

Description

The IRLZ34N uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a

Battery protection or in other Switching application.

Application

Battery protection
 Load switch
 Uninterruptible power supply

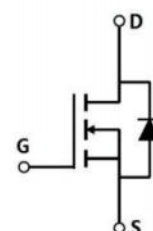
General Features

$V_{DS} = 60V$ $I_D = 50A$

$R_{DS(ON)} < 15m\Omega$ @ $V_{GS}=10V$

$R_{DS(ON)} < 18m\Omega$ @ $V_{GS}=4.5V$

TO220-3L Pin Configuration



Absolute Maximum Ratings ($T_C=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	60	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_C=25^\circ\text{C}$	Continuous Drain Current, V_{GS} @ 10V ¹	50	A
$I_D@T_C=100^\circ\text{C}$	Continuous Drain Current, V_{GS} @ 10V ¹	25	A
$I_D@T_A=25^\circ\text{C}$	Continuous Drain Current, V_{GS} @ 10V ¹	7.4	A
$I_D@T_A=70^\circ\text{C}$	Continuous Drain Current, V_{GS} @ 10V ¹	6	A
I_{DM}	Pulsed Drain Current ²	90	A
EAS	Single Pulse Avalanche Energy ³	39.2	mJ
I_{AS}	Avalanche Current	28	A
$P_D@T_C=25^\circ\text{C}$	Total Power Dissipation ⁴	45	W
$P_D@T_A=25^\circ\text{C}$	Total Power Dissipation ⁴	2	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	62	$^\circ\text{C/W}$

60V N-Channel Enhancement Mode MOSFET

$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	2.8	°C/W
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Electrical Characteristics ($T_J=25^{\circ}\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	60	---	---	V
$\Delta BV_{DSS}/\Delta T_J$	BV_{DSS} Temperature Coefficient	Reference to 25°C , $I_D=1mA$	---	0.057	---	V/°C
$R_{DS(ON)}$	Static Drain-Source On-Resistance ²	$V_{GS}=10V, I_D=20A$	---	10	15	mΩ
		$V_{GS}=4.5V, I_D=10A$	---	13	18	
$V_{GS(th)}$	Gate Threshold Voltage		1.2	---	2.5	V
$\Delta V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient	$V_{GS}=V_{DS}, I_D=250\mu A$	---	-5.68	---	mV/°C
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=48V, V_{GS}=0V, T_J=25^{\circ}\text{C}$	---	---	1	uA
		$V_{DS}=48V, V_{GS}=0V, T_J=55^{\circ}\text{C}$	---	---	5	
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	---	---	± 100	nA
g_{fs}	Forward Transconductance	$V_{DS}=5V, I_D=15A$	---	45	---	S
R_g	Gate Resistance	$V_{DS}=0V, V_{GS}=0V, f=1MHz$	---	1.7	---	Ω
Q_g	Total Gate Charge (4.5V)		---	19.3	---	nC
Q_{gs}	Gate-Source Charge	$V_{DS}=48V, V_{GS}=4.5V, I_D=15A$	---	7.1	---	
Q_{gd}	Gate-Drain Charge		---	7.6	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=30V, V_{GS}=10V, R_G=3.3\Omega, I_D=15A$	---	7.2	---	ns
T_r	Rise Time		---	50	---	
$T_{d(off)}$	Turn-Off Delay Time		---	36.4	---	
T_f	Fall Time		---	7.6	---	
C_{iss}	Input Capacitance	$V_{DS}=15V, V_{GS}=0V, f=1MHz$	---	2423	---	pF
C_{oss}	Output Capacitance		---	145	---	
C_{rss}	Reverse Transfer Capacitance		---	97	---	
I_S	Continuous Source Current ^{1,5}	$V_G=V_D=0V, \text{Force Current}$	---	---	35	A
I_{SM}	Pulsed Source Current ^{2,5}		---	---	80	A
V_{SD}	Diode Forward Voltage ²	$V_{GS}=0V, I_S=A, T_J=25^{\circ}\text{C}$	---	---	1	V
t_{rr}	Reverse Recovery Time	$I_F=15A, di/dt=100A/\mu s, T_J=25^{\circ}\text{C}$	---	16.3	---	nS
Q_{rr}	Reverse Recovery Charge		---	11	---	nC

Note :

1.The data tested by surface mounted on a 1 inch² FR-4 board with 20Z copper.

2.The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$

3.The EAS data shows Max. rating . The test condition is $V_{DD}=25V, V_{GS}=10V, L=0.1mH, I_{AS}=28A$

4.The power dissipation is limited by 150°C junction temperature 5.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation

Typical Characteristics

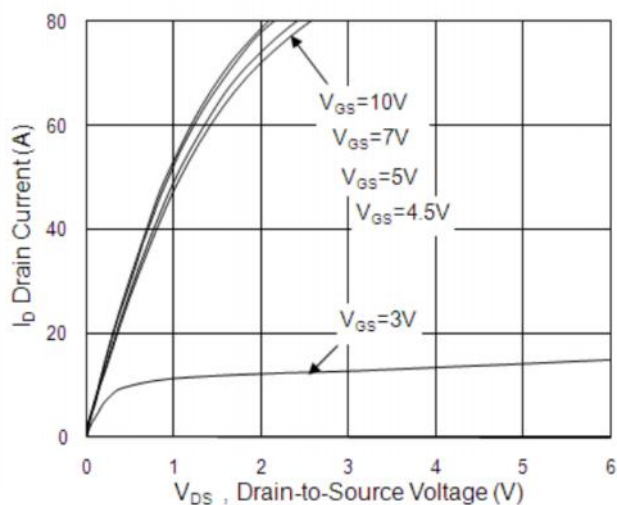


Fig.1 Typical Output Characteristics

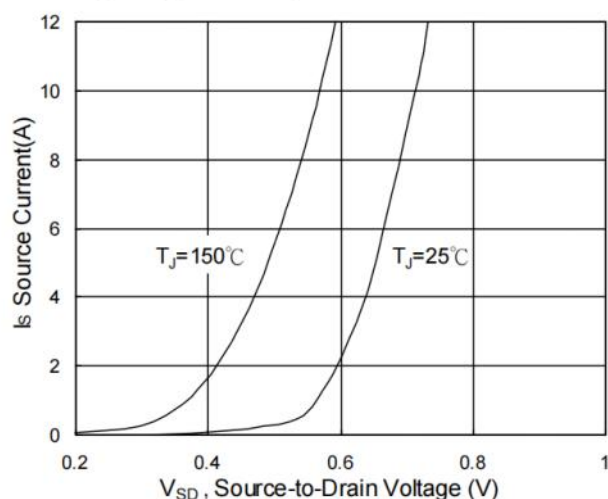


Fig.3 Forward Characteristics of Reverse

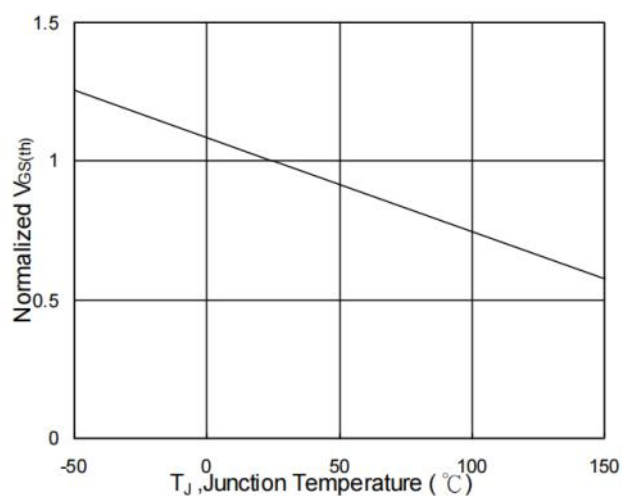


Fig.5 Normalized $V_{GS(th)}$ v.s T_J

60V N-Channel Enhancement Mode MOSFET

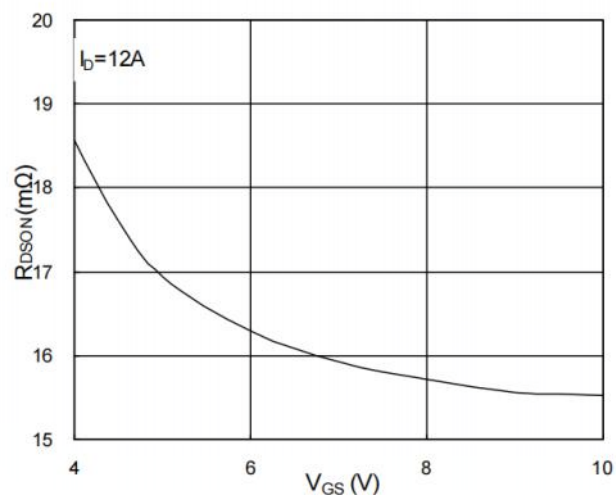


Fig.2 On-Resistance v.s Gate-Source

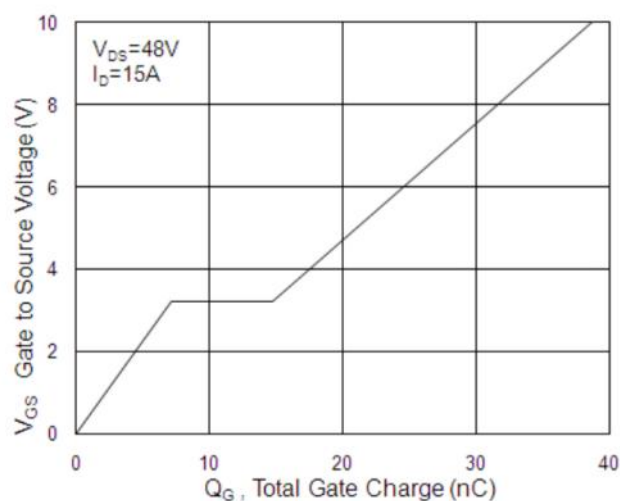


Fig.4 Gate-Charge Characteristics

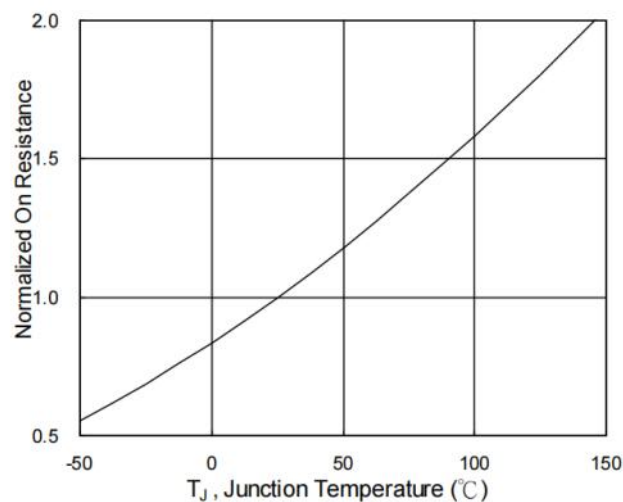
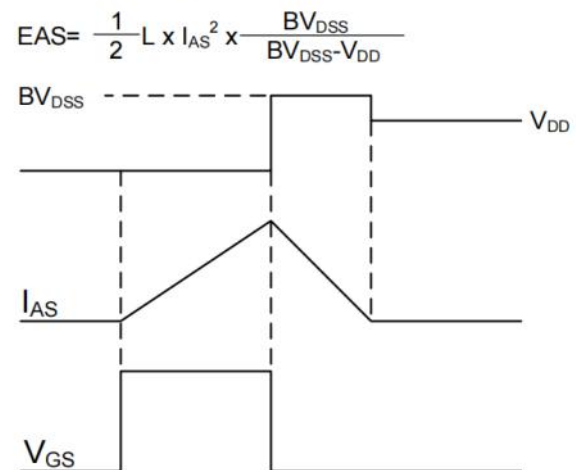
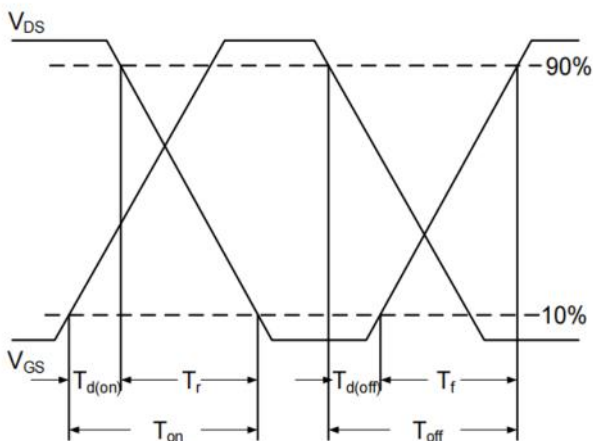
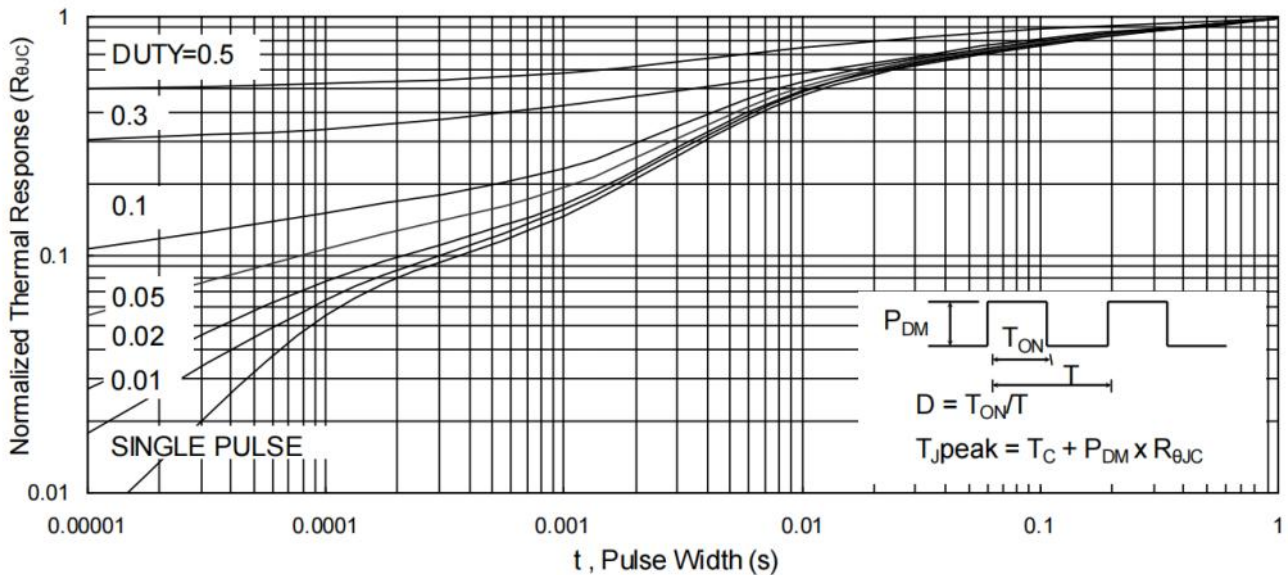
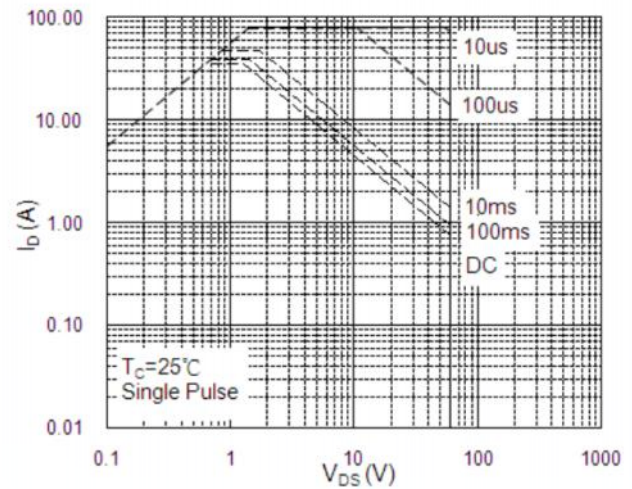
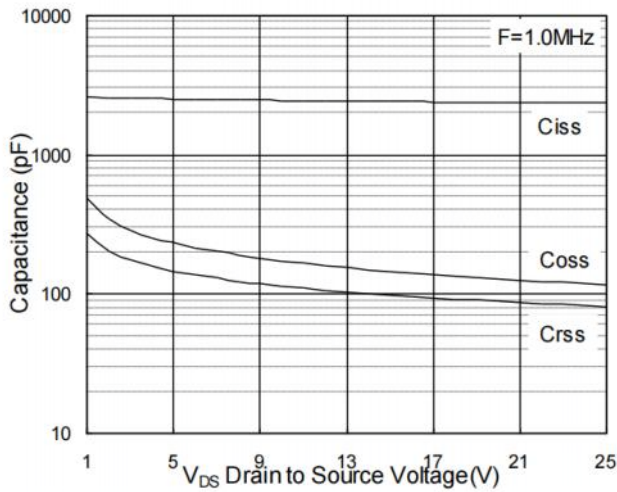
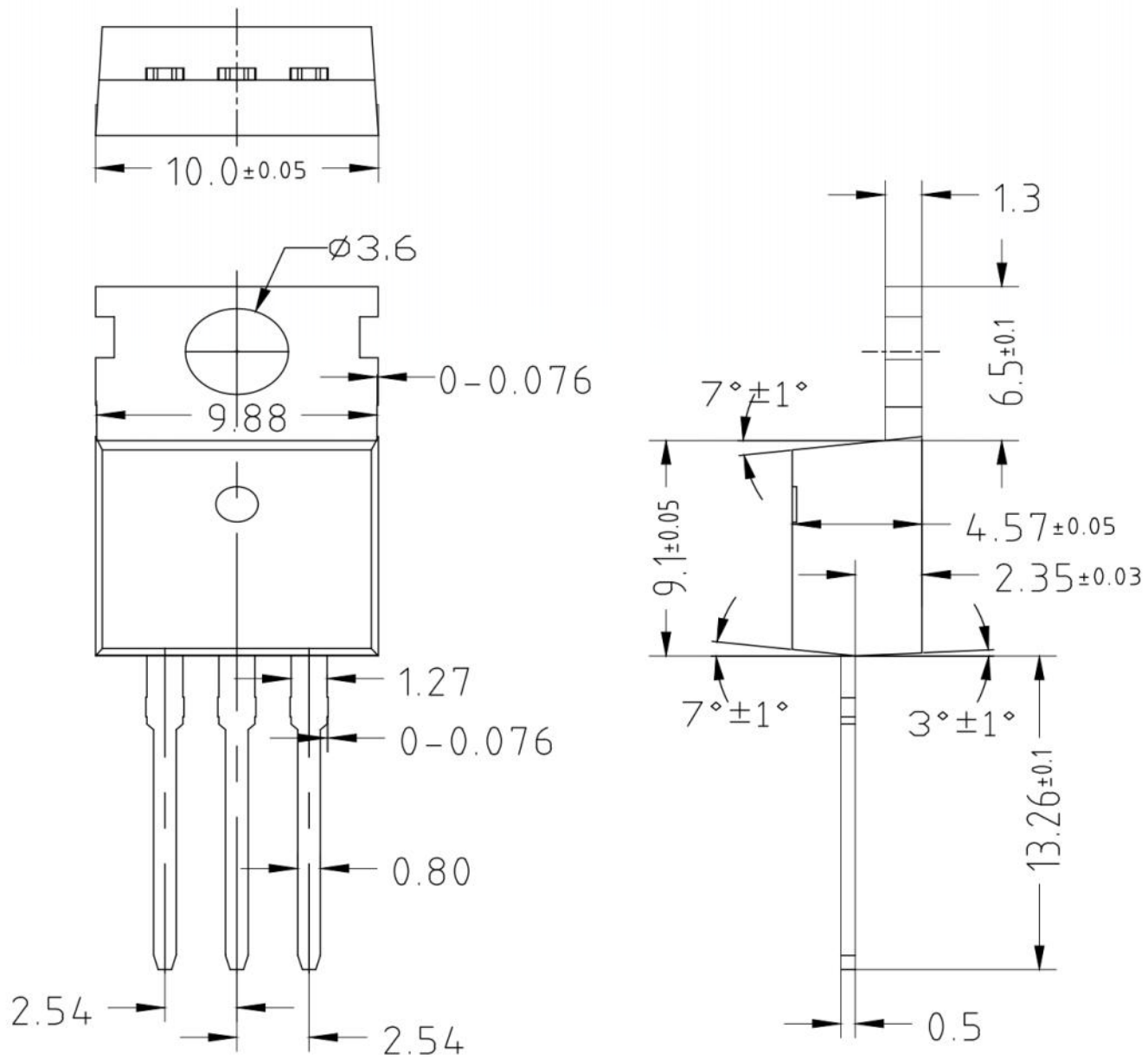


Fig.6 Normalized $R_{DS(on)}$ v.s T_J

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